

100A, 70V N-CHANNEL MOSFET

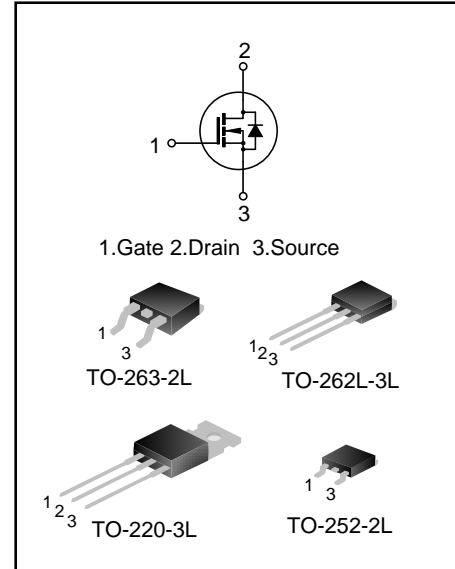
DESCRIPTION

SVG076R5NT(S)(D)(KL) is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan's LVMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance.

This device is widely used in UPS, Power Management for Inverter Systems.

FEATURES

- ◆ 100A, 70V, $R_{DS(on)(typ.)}=5.4m\Omega@V_{GS}=10V$
- ◆ Low gate charge
- ◆ Low Crss
- ◆ Fast switching
- ◆ Improved dv/dt capability



ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVG076R5NT	TO-220-3L	076R5NT	Pb free	Tube
SVG076R5NS	TO-263-2L	076R5NS	Halogen free	Tube
SVG076R5NSTR	TO-263-2L	076R5NS	Halogen free	Tape & Reel
SVG076R5NDTR	TO-252-2L	076R5ND	Halogen free	Tape & Reel
SVG076R5NKL	TO-262L-3L	076R5NKL	Pb free	Tube

ABSOLUTE MAXIMUM RATINGS (UNLESS OTHERWISE NOTED, T_C=25°C)

Characteristics	Symbol	Ratings		Unit
		SVG076R5NT/NS/NKL	SVG076R5ND	
Drain-Source Voltage	V _{DS}	70		V
Gate-Source Voltage	V _{GS}	±20		V
Drain Current	I _D	T _C =25°C	100	A
		T _C =100°C	63	
Drain Current Pulsed	I _{DM}	400		A
Power Dissipation (T _C =25°C) -Derate above 25°C	P _D	114	96	W
		0.91	0.77	W/°C
Single Pulsed Avalanche Energy (Note 1)	E _{AS}	280		mJ
Operation Junction Temperature Range	T _J	-55~+150		°C
Storage Temperature Range	T _{stg}	-55~+150		°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Ratings		Unit
		SVG076R5NT/NS/NKL	SVG076R5ND	
Thermal Resistance, Junction-to-Case	R _{θJC}	1.1	1.3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	62.0	°C/W

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, T_C=25°C)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	70	--	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =70V, V _{GS} =0V	--	--	1.0	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =40A	--	5.4	6.5	mΩ
Gate Resistance	R _G	f=1MHz	--	2.1	--	Ω
Input Capacitance	C _{iss}	f=1MHz, V _{GS} =0V, V _{DS} =35V	--	3052	--	pF
Output Capacitance	C _{oss}		--	479	--	
Reverse Transfer Capacitance	C _{rss}		--	24	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} =35V, V _{GS} =10V, R _G =2.7Ω, I _D =40A (Note 2,3)	--	20	--	ns
Turn-on Rise Time	t _r		--	35	--	
Turn-off Delay Time	t _{d(off)}		--	37	--	
Turn-off Fall Time	t _f		--	12	--	
Total Gate Charge	Q _g	V _{DD} =56V, V _{GS} =10V, I _D =40A (Note 2,3)	--	50	--	nC
Gate-Source Charge	Q _{gs}		--	20	--	
Gate-Drain Charge	Q _{gd}		--	12	--	

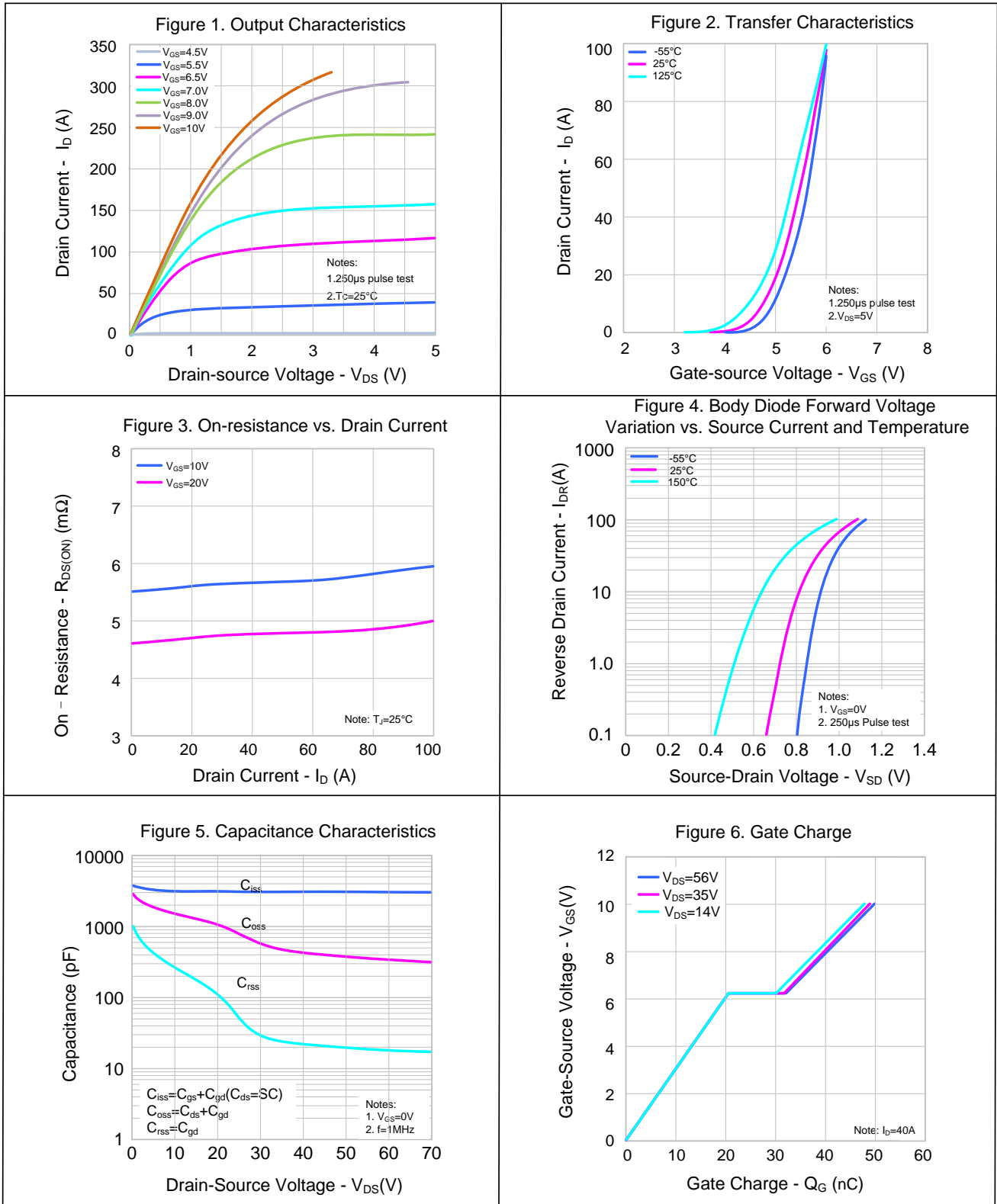
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction	--	--	100	A
Pulsed Source Current	I_{SM}	Diode in the MOSFET	--	--	400	
Diode Forward Voltage	V_{SD}	$I_S=40A, V_{GS}=0V$	--	--	1.4	V
Reverse Recovery Time	T_{rr}	$I_S=40A, V_{GS}=0V, dI/dt=100A/\mu s$	--	45	--	ns
Reverse Recovery Charge	Q_{rr}	(Note 2)	--	0.06	--	μC

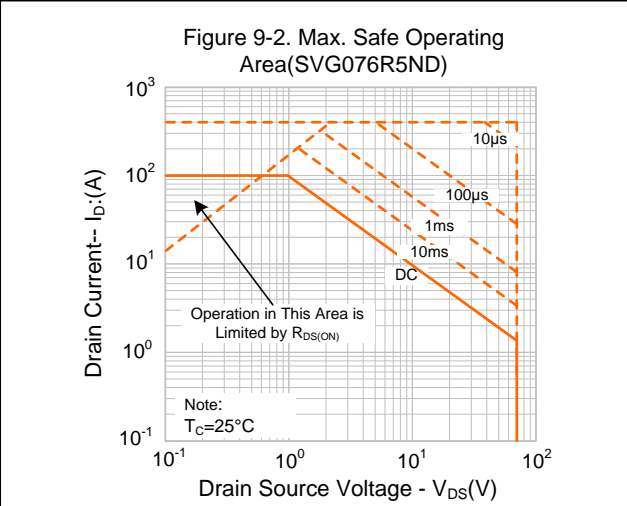
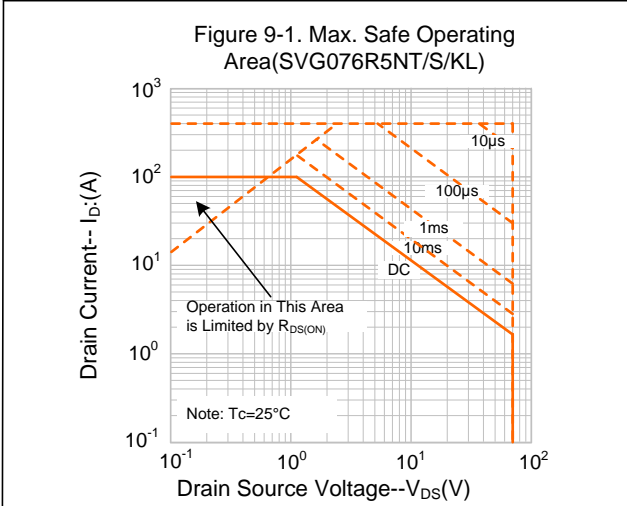
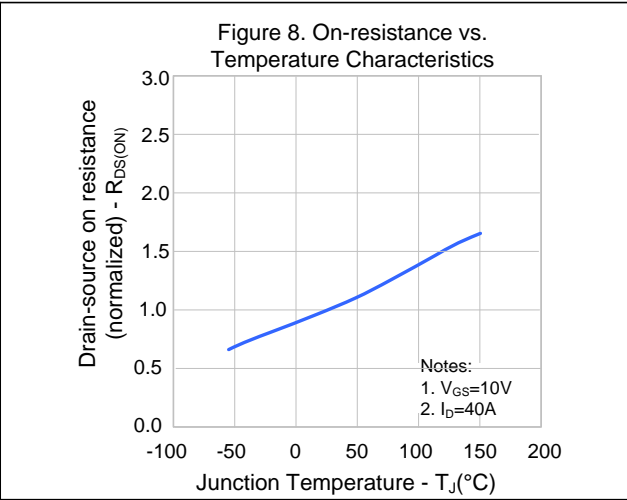
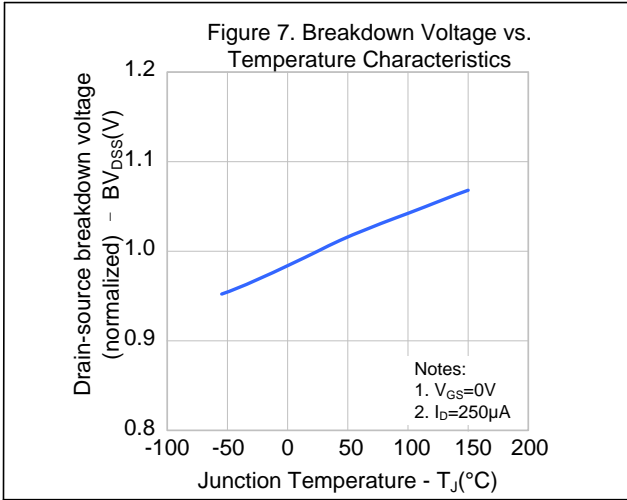
Notes:

1. $L=0.5mH, I_{AS}=32A, V_{DD}=56V, R_G=25\Omega$, starting $T_J=25^\circ C$;
2. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

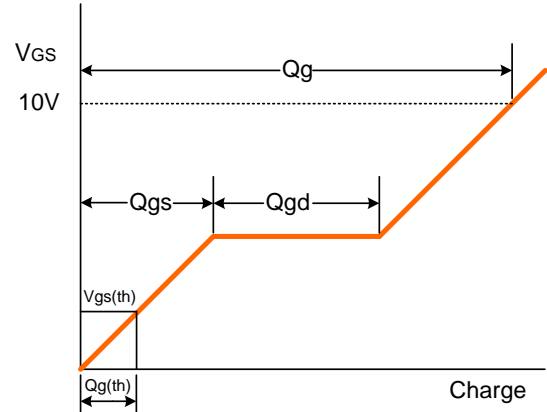
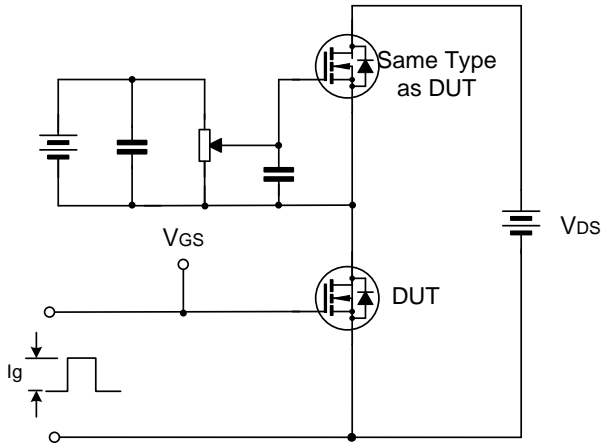


TYPICAL CHARACTERISTICS (CONTINUED)

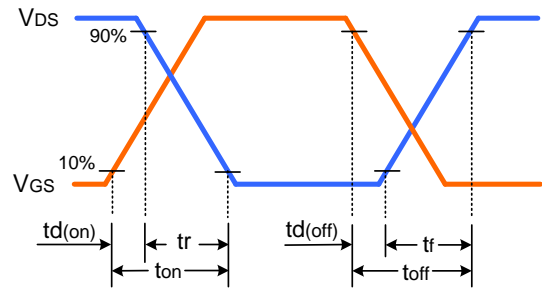
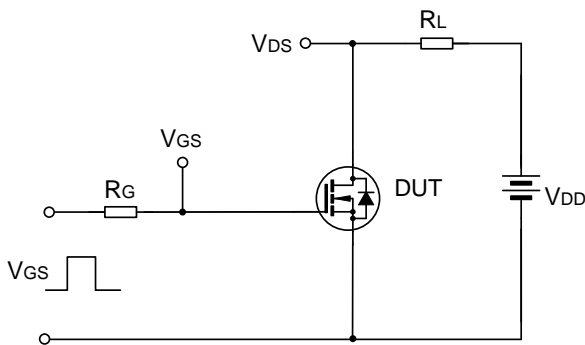


TYPICAL TEST CIRCUIT

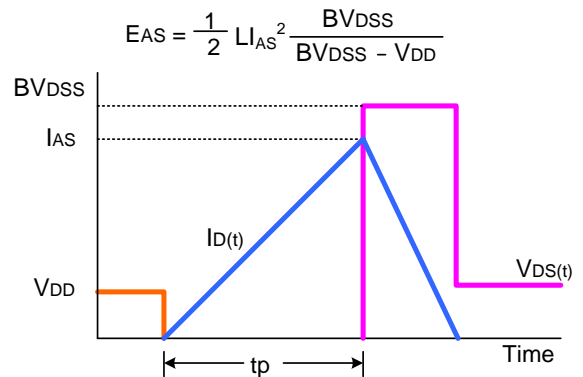
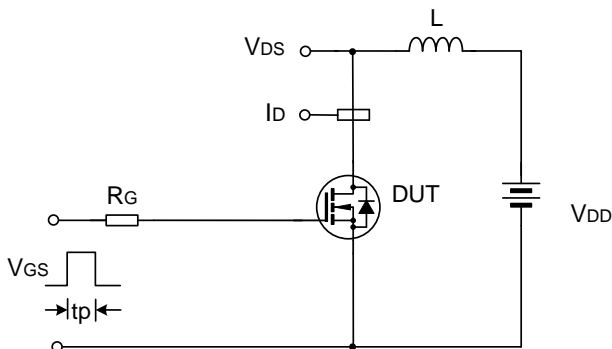
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform

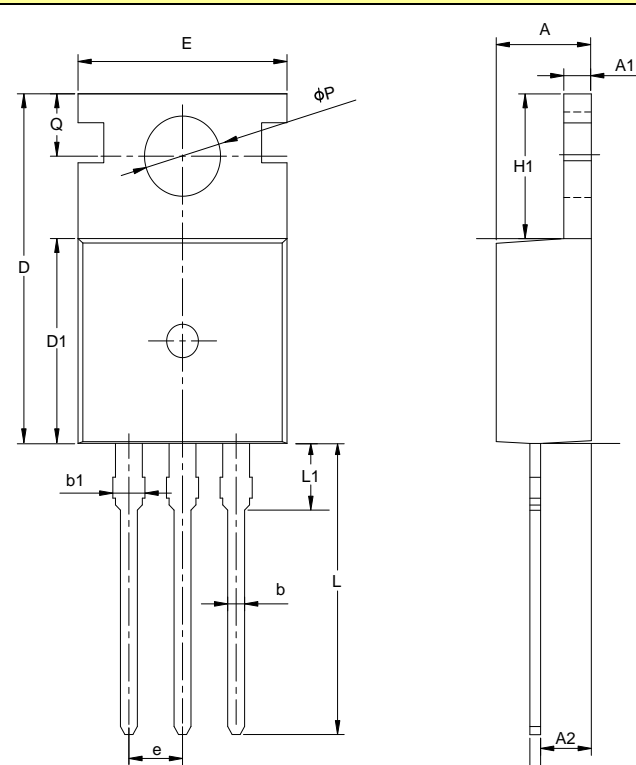


Unclamped Inductive Switching Test Circuit & Waveform



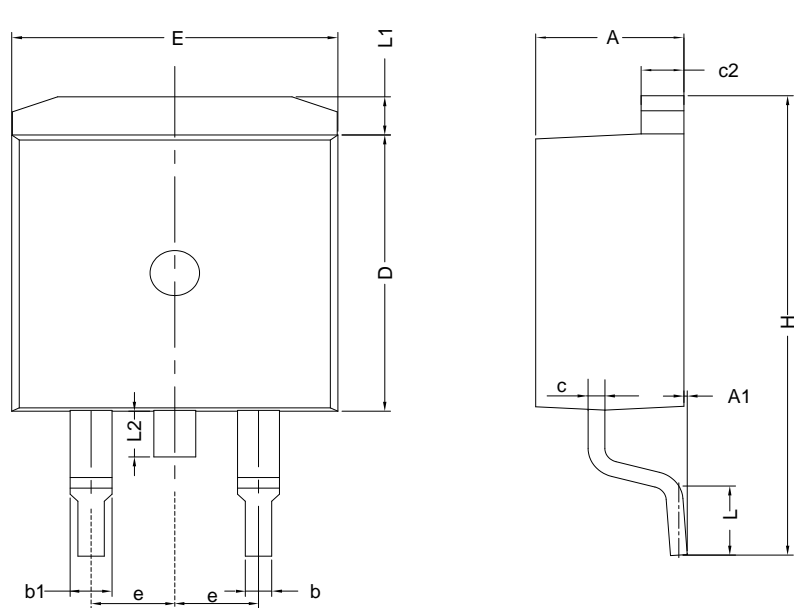
PACKAGE OUTLINE

TO-220-3L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.00	1.30	1.50
A2	1.80	2.40	2.80
b	0.60	0.80	1.00
b1	1.00	—	1.60
c	0.30	—	0.70
D	15.10	15.70	16.10
D1	8.10	9.20	10.00
E	9.60	9.90	10.40
e	2.54BSC		
H1	6.10	6.50	7.00
L	12.60	13.08	13.60
L1	—	—	3.95
φP	3.40	3.70	3.90
Q	2.60	—	3.20

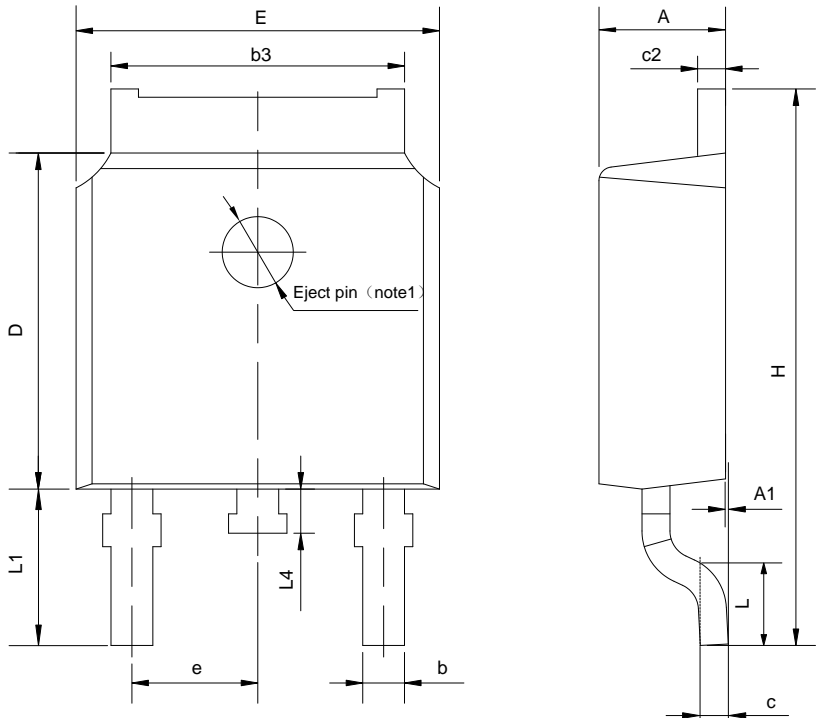
TO-263-2L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.57	4.72
A1	0	0.10	0.25
b	0.71	0.81	0.91
b1	1.17	—	1.50
c	0.30	—	0.60
c2	1.17	1.27	1.37
D	8.50	—	9.35
E	9.80	—	10.45
e	2.54BSC		
H	14.70	—	15.75
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	—	—	1.75

PACKAGE OUTLINE (CONTINUED)

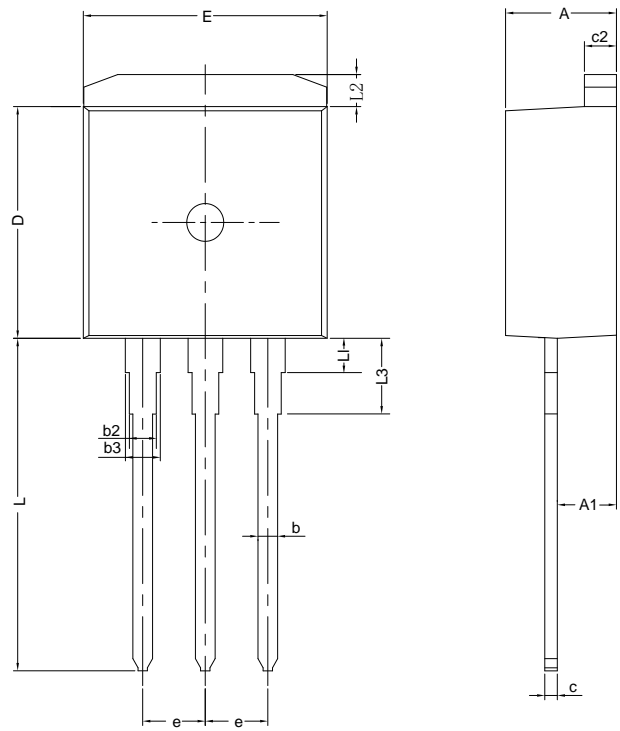
TO-252-2L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.10	2.30	2.50
A1	0	—	0.127
b	0.66	0.76	0.89
b3	5.10	5.33	5.46
c	0.45	—	0.65
c2	0.45	—	0.65
D	5.80	6.10	6.40
E	6.30	6.60	6.90
e	2.30TYP		
H	9.60	10.10	10.60
L	1.40	1.50	1.70
L1	2.90REF		
L4	0.60	0.80	1.00

NOTE1 : There are two conditions for this position:has an eject pin or has no eject pin.

TO-262L-3L **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	2.20	—	2.92
b	0.71	0.80	0.88
b2	0.90	1.01	1.08
b3	1.20	—	1.50
c	0.34	—	0.76
c2	1.22	1.30	1.35
D	8.38	—	9.30
E	9.80	10.16	10.54
e	2.54 BSC		
L	12.80	—	14.10
L1	1.40	1.50	1.60
L2	1.12	—	1.42
L3	3.00	3.20	3.40

Important notice :

1. The instructions are subject to change without notice!
2. Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current. Please read the instructions carefully before using our products, including the circuit operation precautions.
3. Our products are consumer electronic products or the other civil electronic products.
4. When using our products, please do not exceed the maximum rating of the products, otherwise the reliability of the whole machine will be affected. There is a certain possibility of failure or malfunction of any semiconductor product under specific conditions. The buyer is responsible for complying with safety standards and taking safety measures when using our products for system design, sample and whole machine manufacturing, so as to avoid potential failure risk that may cause personal injury or property loss.
5. It is strongly recommended to identify the trademark when buying our products. Please contact us if there is any question.
6. Product promotion is endless, our company will wholeheartedly provide customers with better products!
7. Website: <http://www.silan.com.cn>

Part No.:	SVG076R5NT(S)(D)(KL)	Document Type:	Datasheet
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Rev.: 1.2

Revision History:

1. Add package of SVG076R5NKL
2. Update typical test circuit and important notice
3. Delete nomenclature

Rev.: 1.1

Revision History:

1. Add package outline of To-263-2L and To-252-2L
2. Modify electrical diagram and typical circuit diagram
3. Add SOA curve of SVG076R5ND

Rev.: 1.0

Revision History:

1. First release
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